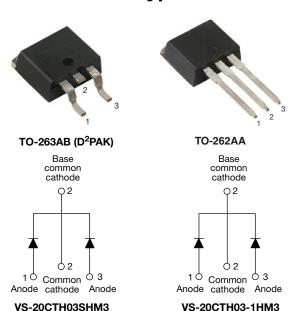


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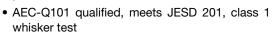
# Hyperfast Rectifier, 2 x 10 A FRED Pt®



PRODUCT SUMMARY								
Package	TO-263AB (D <sup>2</sup> PAK), TO-262AA							
I <sub>F(AV)</sub>	2 x 10 A							
$V_{R}$	300 V							
V <sub>F</sub> at I <sub>F</sub>	0.85 V							
t <sub>rr</sub> typ.	23 ns							
T <sub>J</sub> max.	175 °C							
Diode variation	Common cathode							

#### **FEATURES**

- Hyperfast recovery time
- Low forward voltage drop
- Low leakage current
- 175 °C operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C









#### ROHS COMPLIANT HALOGEN FREE

#### **DESCRIPTION / APPLICATIONS**

Vishay Semiconductors 300 V series are the state of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER		SYMBOL	TEST CONDITIONS	MAX.	UNITS				
Peak repetitive reverse voltage		$V_{RRM}$		300	V				
A construction of the construction	per diode		T <sub>C</sub> = 160 °C	10					
Average rectified forward current	per device	I <sub>F(AV)</sub>		20	Α				
Non-repetitive peak surge current		I <sub>FSM</sub>	T <sub>J</sub> = 25 °C	120					
Operating junction and storage ten	nperatures	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C				

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μA	300	-	-			
Forward voltage	$V_{F}$	I <sub>F</sub> = 10 A	-	1.05	1.25	V		
		I <sub>F</sub> = 10 A, T <sub>J</sub> = 125 °C	-	0.85	0.95	1		
Reverse leakage current	I_	$V_R = V_R$ rated	-	-	20	μA		
neverse leakage current	I <sub>R</sub>	$T_J = 125  ^{\circ}\text{C},  V_R = V_R  \text{rated}$	-	6	200	μΑ		
Junction capacitance	C <sub>T</sub>	$V_{R} = 300 \text{ V}$	-	30	-	pF		
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8	-	nH		

# VS-20CTH03SHM3, VS-20CTH03-1HM3

# Vishay Semiconductors

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>C</sub> = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
		I <sub>F</sub> = 1.0 A, dI <sub>F</sub> /dt =	$I_F = 1.0 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$			-			
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	31	-	ns		
		T <sub>J</sub> = 125 °C		-	42	-			
Dook receivent ourrent	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C	I <sub>F</sub> = 10 A dI <sub>F</sub> /dt = 200 A/μs	-	2.4	-	Α		
Peak recovery current		T <sub>J</sub> = 125 °C	$V_{\rm R} = 200 \text{ V}$	ı	5.6	1			
Poverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 25 °C	] ''	- 1	36	-	nC		
Reverse recovery charge		T <sub>J</sub> = 125 °C		-	120	-	nC		

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55	-	175	°C			
Thermal resistance, junction to case per diode	R <sub>thJC</sub>		-	-	1.5	°C/W			
Weight			-	2.0	-	g			
Weight			-	0.07	-	OZ.			
Marking device		Case style TO-263AB (D²PAK)         20CTH03SH           Case style TO-262AA         20CTH03-1H			H03SH	-			
					20CTH03-1H				

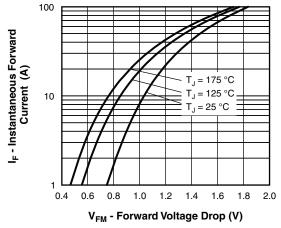


Fig. 1 - Maximum Forward Voltage Drop Characteristics

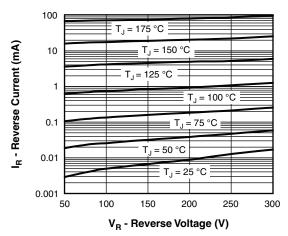


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

## Vishay Semiconductors

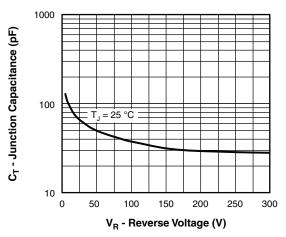


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

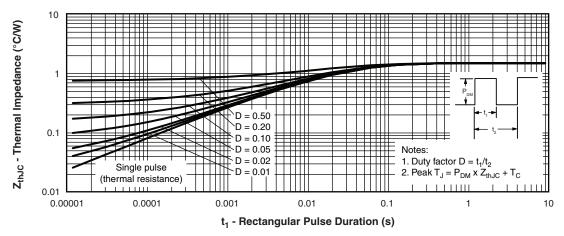


Fig. 4 - Maximum Thermal Impedance  $Z_{thJC}$  Characteristics

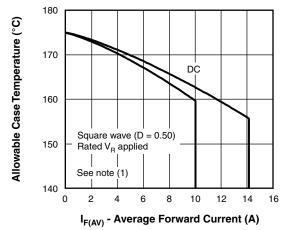


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

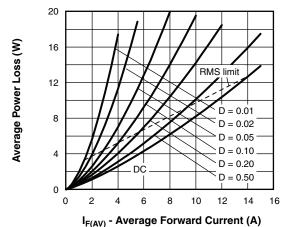


Fig. 6 - Forward Power Loss Characteristics

## Note

 $\begin{array}{ll} \text{(1)} \ \ \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}; \\ Pd = \text{forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 6)}; \\ Pd_{REV} = \text{inverse power loss} = V_{R1} \times I_R \text{ (1 - D); } I_R \text{ at } V_{R1} = \text{rated } V_R \\ \end{array}$ 

# VS-20CTH03SHM3, VS-20CTH03-1HM3

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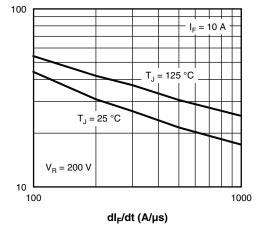


Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

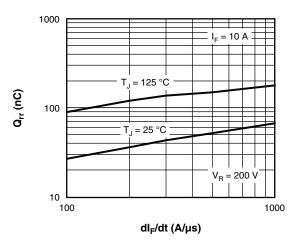
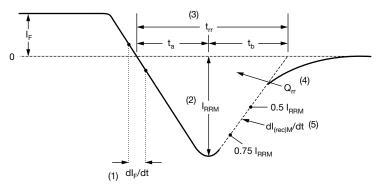


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt



- (1) dl<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $I_{RRM}$  peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm I_F$  to point where a line passing through 0.75  $\rm I_{RRM}$  and 0.50  $\rm I_{RRM}$  extrapolated to zero current.
- (4)  $\mathbf{Q}_{rr}$  area under curve defined by  $\mathbf{t}_{rr}$  and  $\mathbf{I}_{\mathrm{RRM}}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5)  $dl_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$ 

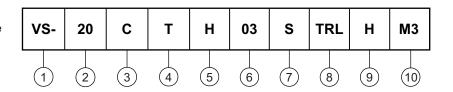
Fig. 9 - Reverse Recovery Waveform and Definitions

# VS-20CTH03SHM3, VS-20CTH03-1HM3

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## **ORDERING INFORMATION TABLE**

Device code



1 - Vishay Semiconductors product

2 - Current rating (20 A)

C = common cathode

4 -  $T = TO-220, D^2PAK$ 

5 - H = hyperfast rectifier

Voltage rating (03 = 300 V)

7 - • S = D<sup>2</sup>PAK

• -1 = TO-262

None = tube (50 pieces)

• TRL = tape and reel (left oriented, for D<sup>2</sup>PAK package)

• TRR = tape and reel (right oriented, for D<sup>2</sup>PAK package)

9 - H = AEC-Q101 qualified

10 - M3 = halogen-free, RoHS-compliant, and termination lead (Pb)-free

LINKS TO RELATED DOCUMENTS						
Dimensions	TO-263AB (D <sup>2</sup> PAK)	www.vishay.com/doc?95046				
Differsions	TO-262AA	www.vishay.com/doc?95419				
Part marking information	TO-263AB (D <sup>2</sup> PAK)	www.vishay.com/doc?95444				
Part marking information	TO-262AA	www.vishay.com/doc?95443				
Packaging information	TO-263AB (D <sup>2</sup> PAK)	www.vishay.com/doc?95032				



## Vishay Semiconductors

## D<sup>2</sup>PAK

#### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES		SYMBOL	MILLIM	ETERS	INC	HES	NOTES
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOIES	NOTES	STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	) BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

#### Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC® outline TO-263AB

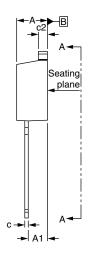


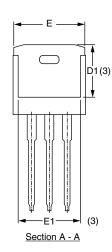
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## **TO-262**

#### **DIMENSIONS** in millimeters and inches

# 



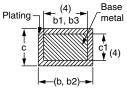


**⊕** 0.010**⋒**|A**⋒**|B

### Lead assignments



<u>Diodes</u>
1. - Anode (two die)/open (one die)
2., 4. - Cathode
3. - Anode



Section B - B and C - C Scale: None

CYMPOL	MILLIN	METERS	INC	INCHES			
SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES		
А	4.06	4.83	0.160	0.190			
A1	2.03	3.02	0.080	0.119			
b	0.51	0.99	0.020	0.039			
b1	0.51	0.89	0.020	0.035	4		
b2	1.14	1.78	0.045	0.070			
b3	1.14	1.73	0.045	0.068	4		
С	0.38	0.74	0.015	0.029			
c1	0.38	0.58	0.015	0.023	4		
c2	1.14	1.65	0.045	0.065			
D	8.51	9.65	0.335	0.380	2		
D1	6.86	8.00	0.270	0.315	3		
Е	9.65	10.67	0.380	0.420	2, 3		
E1	7.90	8.80	0.311	0.346	3		
е	2.54 BSC		0.100 BSC				
L	13.46	14.10	0.530	0.555			
L1	=	1.65	-	0.065	3		
L2	3.56	3.71	0.140	0.146			

#### Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- $^{(3)}$  Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Controlling dimension: inches
- (6) Outline conform to JEDEC TO-262 except A1 (maximum), b (minimum) and D1 (minimum) where dimensions derived the actual package outline



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Vishay

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